

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

77

1.-~~76~~. (Canceled)

78. (Currently Amended) A semiconductor device comprising:

a semiconductor layer including a channel region and source and drain regions in contact with said channel region at a source-channel boundary and a drain-channel boundary, respectively, wherein said channel region comprises semi-amorphous silicon;

a gate electrode adjacent to said channel region with a gate insulating film interposed therebetween; and

a region formed in the vicinity of at least one of said source-channel boundary and said drain-channel boundary in said semiconductor layer, said region containing one or more elements selected from the group consisting of carbon, nitrogen, and oxygen at a concentration of 1×10^{19} atoms/cm³ or more,

wherein one boundary of said region is located within the channel region and is not aligned with edges of the gate electrode, and the other boundary is located within one of the source region and said drain region.

79. (Previously Presented) A device according to claim 78 wherein said semiconductor layer is an active layer of a thin film transistor selected from the group consisting of stagger type, inverted stagger type, planar type, and inverted planar type transistors.

80.-81. (Canceled)